

Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
 STATEMENT BY APPLICANT**  
*(Use as many sheets as necessary)*

PTO/SB/08A(10-01)  
 FEB 20 2006  
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Complete if Known

<b>Application Number</b>	10/075484
<b>Filing Date</b>	February 12, 2002
<b>First Named Inventor</b>	Bhattacharyya, Arup
<b>Group Art Unit</b>	2818
<b>Examiner Name</b>	Phan, Trong

Sheet 1 of 3

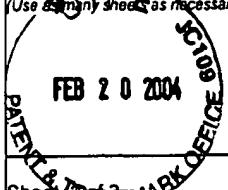
Attorney Docket No: 1303.043US1

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 FEB 20 2004 Sheet 1 of 1		<table border="1"> <tr> <td><b>Application Number</b></td> <td colspan="4">10/075484</td> </tr> <tr> <td><b>Filing Date</b></td> <td colspan="4">February 12, 2002</td> </tr> <tr> <td><b>First Named Inventor</b></td> <td colspan="4">Bhattacharyya, Arup</td> </tr> <tr> <td><b>Group Art Unit</b></td> <td colspan="4">2818</td> </tr> <tr> <td><b>Examiner Name</b></td> <td colspan="4">Phan, Trong</td> </tr> </table>					<b>Application Number</b>	10/075484				<b>Filing Date</b>	February 12, 2002				<b>First Named Inventor</b>	Bhattacharyya, Arup				<b>Group Art Unit</b>	2818				<b>Examiner Name</b>	Phan, Trong			
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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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